

Title (en)

BYPASSED GATE TRANSISTORS HAVING IMPROVED STABILITY

Title (de)

BYPASS-GATE-TRANSISTOREN MIT VERBESSERTER STABILITÄT

Title (fr)

TRANSISTORS À GRILLE CONTOURNÉS AYANT UNE STABILITÉ AMÉLIORÉE

Publication

EP 4393009 A1 20240703 (EN)

Application

EP 22769536 A 20220826

Priority

- US 202117492032 A 20211001
- US 2022075500 W 20220826

Abstract (en)

[origin: WO2023056145A1] A transistor device includes a plurality of gate fingers that extend in a first direction and are spaced apart from each other in a second direction, each of the gate fingers comprising at least spaced-apart and generally collinear first and second gate finger segments that are electrically connected to each other. The first gate finger segments are separated from the second gate finger segments in the first direction by a gap region that extends in the second direction. A resistor is disposed in the gap region.

IPC 8 full level

H01L 23/482 (2006.01); **H01L 29/423** (2006.01); **H01L 29/778** (2006.01)

CPC (source: EP)

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Designated contracting state (EPC)

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